

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S29	164	(257/347.ccls. and 438/406.ccls. 438/455.ccls. 438/458.ccls.) and @pd>"20040916"	US-PGPUB; USPAT	OR	OFF	2005/03/22 17:36
S30	20056	(wafer substrate) with bond\$5 with (separat\$7 delaminat\$5 thin\$7 remov\$7)	US-PGPUB; USPAT	OR	OFF	2005/03/18 18:06
S31	371	S30 and (encapsulat\$5 with (heat\$5 treat\$5))	US-PGPUB; USPAT	OR	OFF	2005/03/18 18:53
S32	26	S31 and (encapsulat\$5 with (heat\$5 treat\$5) with silicon)	US-PGPUB; USPAT	OR	OFF	2005/03/18 18:18
S33	15	encapsulat\$5 with ((heat\$5 treat\$5) near silicon)	US-PGPUB; USPAT	OR	OFF	2005/03/18 18:19
S34	345	S31 not (S32 S33)	US-PGPUB; USPAT	OR	OFF	2005/03/18 19:27
S35	3	?PSG with (flow\$5 reflow\$5) with encapsulat\$5	US-PGPUB; USPAT	OR	OFF	2005/03/18 19:28
S36	249	257/354.ccls. not (257/347.ccls. and 438/406.ccls. 438/455.ccls. 438/458.ccls.)	US-PGPUB; USPAT	OR	OFF	2005/03/22 19:03
S37	2	(psg bpsg) with melt\$5 with heat\$5 with (time minute second)	US-PGPUB; USPAT	OR	OFF	2005/03/22 19:05
S38	0	(psg bpsg) with melt\$5 with rapid with anneal\$5	US-PGPUB; USPAT	OR	OFF	2005/03/22 19:06
S39	155	melt\$5 with rapid with anneal\$5	US-PGPUB; USPAT	OR	OFF	2005/03/22 19:06
S40	1	S39 same (psg bpsg)	US-PGPUB; USPAT	OR	OFF	2005/03/22 19:06
S41	7	(bpsg borophosphosilicate) with heat with (maximum minimum)	US-PGPUB; USPAT	OR	ON	2005/03/24 13:35
S42	0	(bpsg borophosphosilicate psg phosphosilicate) with heat with reflow\$5	US-PGPUB; USPAT	OR	ON	2005/03/24 13:35
S43	1	(bpsg borophosphosilicate psg phosphosilicate) with heat\$5 with reflow\$5	US-PGPUB; USPAT	OR	ON	2005/03/24 13:36
S44	1	(bpsg borophosphosilicate psg phosphosilicate) same (heat\$5 with reflow\$5)	US-PGPUB; USPAT	OR	ON	2005/03/24 13:37
S45	367	(bpsg borophosphosilicate psg phosphosilicate) with heat\$5 with reflow\$5	US-PGPUB; USPAT	OR	ON	2005/03/24 13:37
S46	137	S45 with temperature	US-PGPUB; USPAT	OR	ON	2005/03/24 13:38
S47	48	S46 with (time second\$1 minute\$1 hour\$1 rapid\$2)	US-PGPUB; USPAT	OR	ON	2005/03/24 14:24

S48	63	(silicon on insulator soi) and tft and ((reverse adj gate) bottom gate)	US-PGPUB; USPAT	OR	ON	2005/03/24 14:56
S49	1813	heteroepitaxial	US-PGPUB; USPAT	OR	ON	2005/03/24 14:56
S50	273	S49 same (single crystal monocrystal)	US-PGPUB; USPAT	OR	ON	2005/03/24 14:57
S53	2160	(bpcg borophosphosilicate) and (silicon on insulator soi)	US-PGPUB; USPAT	OR	ON	2005/03/24 19:12
S54	555	S53 and (bonded with (wafer substrate))	US-PGPUB; USPAT	OR	ON	2005/03/24 19:10
S55	41	S54 and ((bpcg borophosphosilicate) with (reflow melt))	US-PGPUB; USPAT	OR	ON	2005/03/24 19:12
S56	578	mosfet and soi and (bonded with oxide)	US-PGPUB; USPAT	OR	ON	2005/03/28 16:55